



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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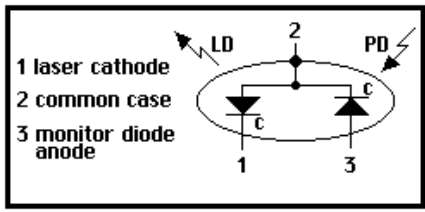
US-Lasers: 780nm-10mW - Infrared Laser Diode and Infrared Diode Laser Module

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TECHNICAL DATA for LASER MODULE		
Barrel Specs: <ul style="list-style-type: none"> 3/8 - 56 Thread Size Dia: 10.4mm Length: 17mm 	Collect Specs: <ul style="list-style-type: none"> 3/8 - 56 Thread Size 4.3mm Aperature Half Hard Brassbbb 	Lens Housing Specs: <ul style="list-style-type: none"> 3/8 - 56 Thread Size 3.7mm Aperture 7mm Plastic Lens

INFRARED DIODE LASER DATA SHEETS

ABSOLUTE MAXIMUM RATINGS - (Tc=25 °C)

TECHNICAL DATA for LASER DIODE		
<ul style="list-style-type: none"> Index Guided MQW Structure Wavelength: 780nm (Typ.) Optical Power: 10mW CW Threshold Current: 45mA (Typ.) Standard Package: 9mm 		
Infrared light output	780nm	Pin Out Diagram - Style A
Optical power output	10mW CW	
Package Type	9mm	
Built-in photo diode for monitoring laser output		

Items	Symbols	Values	Unit
Optical output power	Po	10	mW
Laser diode reverse voltage	VLDR	2	V
Photo diode reverse voltage	VPDR	30	V
Operating temperature	Topr	-10 ~ +40	°C
Storage temperature	Tstg	-40 ~ +85	°C

OPTICAL and ELECTRICAL CHARACTERISTICS - (Tc=25 °C)

Items	Symbols	Min.	Typ.	Max.	Unit	Test Condition
Optical output power	Po	-	10	-	mW	-
Threshold current	Ith	15	25	40	mA	-
Operating current	Iop	30	40	60	mA	Po=10mW
Operating voltage	Vop	2.0	2.4	2.7	V	Po=10mW
Lasing wavelength	λ D	770	780	790	nm	Po=10mW
Beam divergence	θ F	8	10	11	deg	Po=10mW
Beam divergence	θ z	25	31	40	deg	Po=10mW
Slope Efficiency (mW/mA)	η	0.4	0.5	0.7		-
Monitor current	Im	10	30	90	μ A	Po=10mW, Vr=5V
Astigmatism	As	-	11	-	μ m	Po=10mW
MTTF			3000-5,000			Po=10mW, NA=0.4
Emitter Size		1 x 40 Microns				
Emitter Distance to Cap Lens Structure		0.3mm				
		Index Guided				